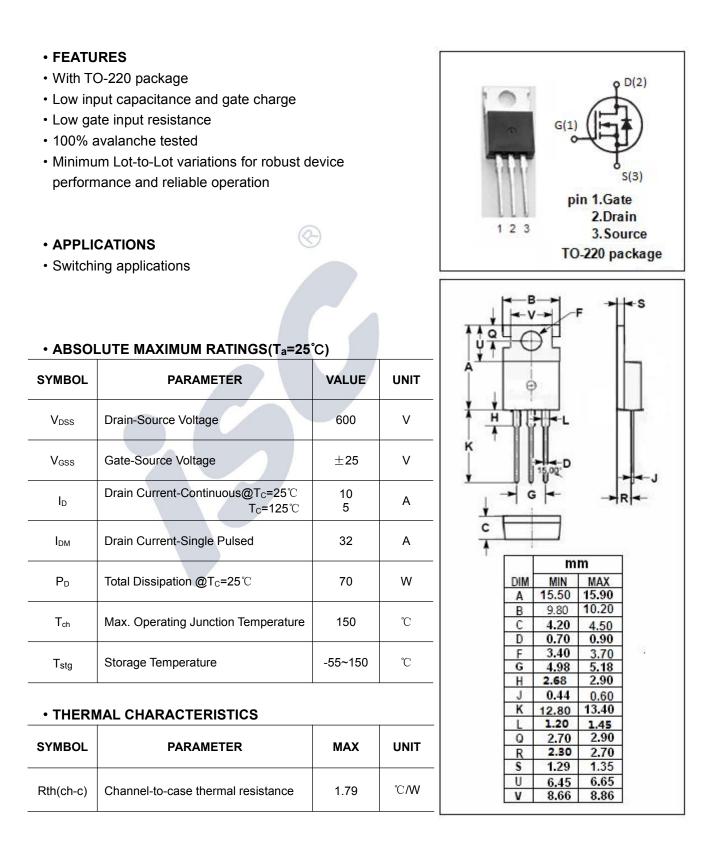


# **Isc N-Channel MOSFET Transistor**

### STP10NM60N



isc website: www.iscsemi.cn

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#### **ELECTRICAL CHARACTERISTICS**

#### $T_{\texttt{C}}\text{=}25^{\circ}\!\!\!\mathbb{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V; I <sub>D</sub> = 1mA	600			v
$V_{GS(th)}$	Gate Threshold Voltage	V <sub>DS</sub> = ±25V; I <sub>D</sub> =0.25mA	2		4	v
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> = 10V; I <sub>D</sub> =4A		60	65	mΩ
lgss	Gate-Source Leakage Current	V <sub>GS</sub> = ±25V;V <sub>DS</sub> = 0V			±0.1	μA
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> = 600V; V <sub>GS</sub> = 0V; T <sub>J</sub> =25°C T <sub>J</sub> =125°C			1 100	μA
VSDF	Diode forward voltage	I <sub>SD</sub> =8A, V <sub>GS</sub> = 0 V			1.3	V

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